



America Semiconductor

**Silicon Power
Schottky Diode**

**MBRT20020 thru
MBRT20040R**

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 200\text{ A}$

Features

- High Surge Capability
- Types up to 100 V V_{RRM}
- Isolation Type Package

Three Tower Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030 (R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 125\text{ }^\circ\text{C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	1500	1500	1500	1500	A
Operating temperature	T_j		-40 to 150	-40 to 150	-40 to 150	-40 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBRT20020 (R)	MBRT20030(R)	MBRT20035 (R)	MBRT20040 (R)	Unit
Diode forward voltage	V_F	$I_F = 100\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	0.75	0.75	0.75	0.75	V
Reverse current	I_R	$V_R = 20\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	1	1	1	1	mA
		$V_R = 20\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	20	20	20	20	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.18	0.18	0.18	0.18	$^\circ\text{C/W}$
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